

A1
index of the p-type cladding layer 10. Consequently, the n-type layer of the opposite conduction type 9 also functions as an optical guide layer.

Please replace the paragraph beginning on page 37, line 1, with the following rewritten paragraph:

A2
As shown in Fig. 9, an n-type layer of the opposite conduction type 9 composed of GaN having a wider bandgap than that of the MQW light emitting layer 8 and having donor levels formed therein is formed on the side of a [0001] direction, that is, on the higher-energy side of the energy band of the MQW light emitting layer 8. The bandgap of the n-type layer of the opposite conduction type 9 is narrower than the bandgap of the p-type cladding layer 10 composed of p-AlGaIn, so that the refraction index of the n-type layer of the opposite conduction type 9 is higher than the refractive index of the p-type cladding layer 10. Consequently, the n-type layer of the opposite conduction type 9 also functions as an optical guide layer..

IN THE CLAIMS:

Please amend claim 35 as follows:

A3
35. (Amended) The light emitting device according to claim 32, wherein
in said barrier layer, more acceptor levels are formed in its portion in contact with an interface of said well layer on the side of said first n-type layer having a higher potential generated as a result of the piezoelectric effect than those in its portion in contact with an interface of said well layer on the side of said first p-type layer having a lower potential.
